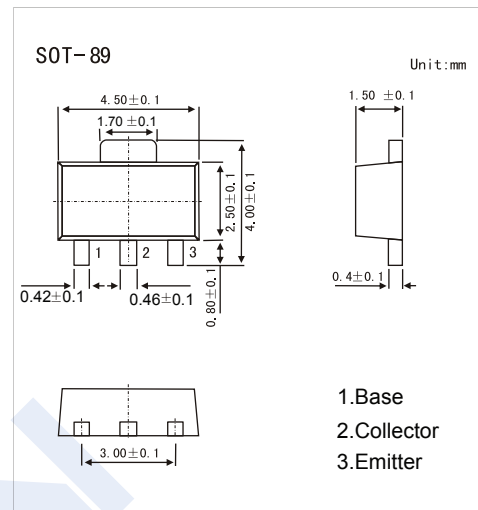


PNP Transistor

2SB772S

■ Features

- PNP transistor High current output up to 3A
- Low Saturation Voltage
- Complement to 2SD882S

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-40	V
Collector to Emitter Voltage	V_{CEO}	-30	V
Emitter to Base Voltage	V_{EBO}	-6	V
Collector Current to Continuous	I_C	-3	A
Collector Dissipation	P_C	0.5	W
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to 150	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V_{CBO}	$I_C = -100\mu\text{A}, I_E = 0$	-40			V
Collector-emitter breakdown voltage	V_{CEO}	$I_C = -10\text{ mA}, I_B = 0$	-30			V
Emitter-base breakdown voltage	V_{EBO}	$I_E = -100\mu\text{A}, I_C = 0$	-6			V
Collector cut-off current	I_{CBO}	$V_{CB} = -40\text{ V}, I_E = 0$			-1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -6\text{ V}, I_C = 0$			-1	μA
DC current gain	h_{FE}	$V_{CE} = -2\text{V}, I_C = -1\text{A}$	60		400	
		$V_{CE} = -2\text{V}, I_C = -100\text{mA}$	32			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -2\text{A}, I_B = -0.2\text{A}$			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -2\text{A}, I_B = -0.2\text{A}$			-1.5	V
Transition frequency	f_T	$V_{CE} = -5\text{ V}, I_C = -0.1\text{mA}, f = 10\text{MHz}$	50			MHz

■ Classification of $h_{fe(1)}$

Type	2SB772S-R	2SB772S-Q	2SB772S-P	2SB772S-E
Range	60-120	100-200	160-320	200-400
Marking	772SR	772SQ	772SP	772SE

PNP Transistor

2SB772S

■ Typical Characteristics

Fig.1 Static characteristics

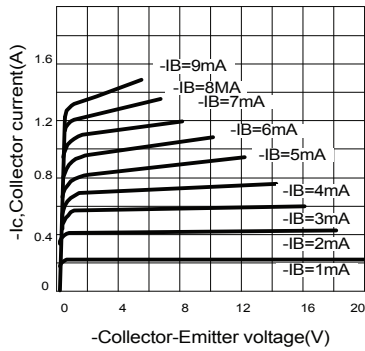


Fig.2 Derating curve of safe operating areas

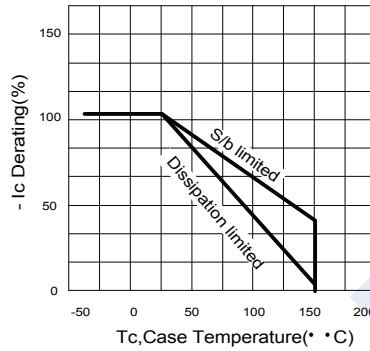


Fig.3 Power Derating

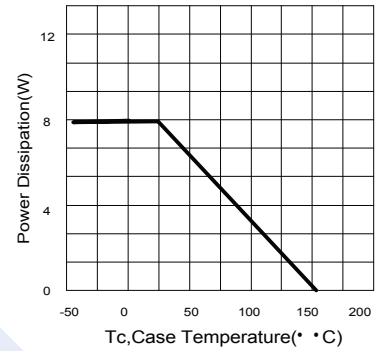


Fig.4 Collector Output capacitance

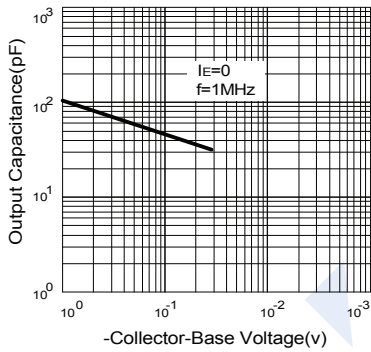


Fig.5 Current gain-bandwidth product

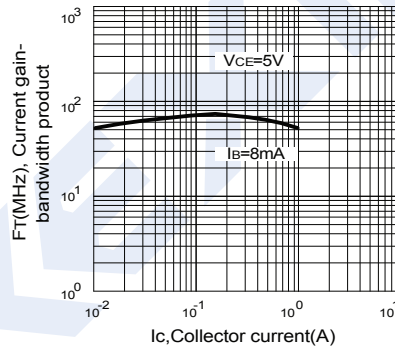


Fig.6 Safe operating area

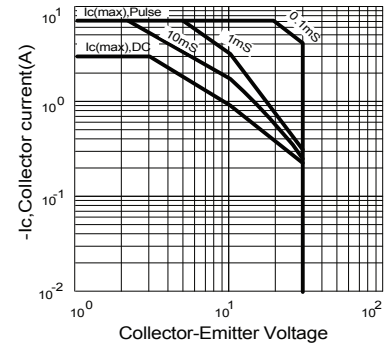


Fig.7 DC current gain

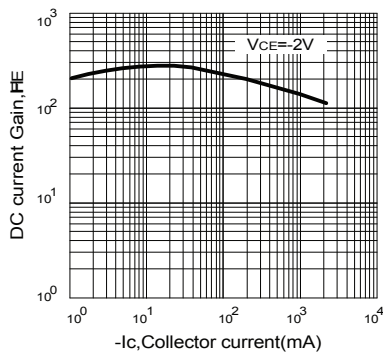


Fig.8 Saturation Voltage

